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Understanding [Embedded - Microprocessors](#)

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of [Embedded - Microprocessors](#)

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details

Product Status	Obsolete
Core Processor	PowerPC e500
Number of Cores/Bus Width	2 Core, 32-Bit
Speed	1.2GHz
Co-Processors/DSP	Signal Processing; SPE, Security; SEC
RAM Controllers	DDR2, DDR3
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (4)
SATA	-
USB	-
Voltage - I/O	1.5V, 1.8V, 2.5V, 3.3V
Operating Temperature	0°C ~ 105°C (TA)
Security Features	Cryptography, Random Number Generator
Package / Case	1023-BFBGA, FCBGA
Supplier Device Package	1023-FCBGA (33x33)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mpc8572elvtatld

- Regular expression (regex) pattern matching
 - Built-in case insensitivity, wildcard support, no pattern explosion
 - Cross-packet pattern detection
 - Fast pattern database compilation and fast incremental updates
 - 16000 patterns, each up to 128 bytes in length
 - Patterns can be split into 256 sets, each of which can contain 16 subsets
- Stateful rule engine enables hardware execution of state-aware logic when a pattern is found
 - Useful for contextual searches, multi-pattern signatures, or for performing additional checks after a pattern is found
 - Capable of capturing and utilizing data from the data stream (such as LENGTH field) and using that information in subsequent pattern searches (for example, positive match only if pattern is detected within the number of bytes specified in the LENGTH field)
 - 8192 stateful rules
- Deflate engine
 - Supports decompression of DEFLATE compression format including zlib and gzip
 - Can work independently or in conjunction with the Pattern Matching Engine (that is decompressed data can be passed directly to the Pattern Matching Engine without further software involvement or memory copying)
- Two Table Lookup Units (TLU)
 - Hardware-based lookup engine offloads table searches from e500 cores
 - Longest prefix match, exact match, chained hash, and flat data table formats
 - Up to 32 tables, with each table up to 16M entries
 - 32-, 64-, 96-, or 128-bit keys
- Two I²C controllers
 - Two-wire interface
 - Multiple master support
 - Master or slave I²C mode support
 - On-chip digital filtering rejects spikes on the bus
- Boot sequencer
 - Optionally loads configuration data from serial ROM at reset the I²C interface
 - Can be used to initialize configuration registers and/or memory
 - Supports extended I²C addressing mode
 - Data integrity checked with preamble signature and CRC
- DUART
 - Two 4-wire interfaces (SIN, SOUT, $\overline{\text{RTS}}$, $\overline{\text{CTS}}$)
 - Programming model compatible with the original 16450 UART and the PC16550D
- Enhanced local bus controller (eLBC)

- Ability to launch DMA from single write transaction
- Serial RapidIO interface unit
 - Supports *RapidIO Interconnect Specification, Revision 1.2*
 - Both 1x and 4x LP-serial link interfaces
 - Long- and short-haul electricals with selectable pre-compensation
 - Transmission rates of 1.25, 2.5, and 3.125 Gbaud (data rates of 1.0, 2.0, and 2.5 Gbps) per lane
 - Auto-detection of 1x- and 4x-mode operation during port initialization
 - Link initialization and synchronization
 - Large and small size transport information field support selectable at initialization time
 - 34-bit addressing
 - Up to 256 bytes data payload
 - All transaction flows and priorities
 - Atomic set/clr/inc/dec for read-modify-write operations
 - Generation of IO_READ_HOME and FLUSH with data for accessing cache-coherent data at a remote memory system
 - Receiver-controlled flow control
 - Error detection, recovery, and time-out for packets and control symbols as required by the RapidIO specification
 - Register and register bit extensions as described in part VIII (Error Management) of the RapidIO specification
 - Hardware recovery only
 - Register support is not required for software-mediated error recovery.
 - Accept-all mode of operation for fail-over support
 - Support for RapidIO error injection
 - Internal LP-serial and application interface-level loopback modes
 - Memory and PHY BIST for at-speed production test
- RapidIO-compliant message unit
 - 4 Kbytes of payload per message
 - Up to sixteen 256-byte segments per message
 - Two inbound data message structures within the inbox
 - Capable of receiving three letters at any mailbox
 - Two outbound data message structures within the outbox
 - Capable of sending three letters simultaneously
 - Single segment multicast to up to 32 devIDs
 - Chaining and direct modes in the outbox
 - Single inbound doorbell message structure
 - Facility to accept port-write messages

2.1.2 Recommended Operating Conditions

Table 2 provides the recommended operating conditions for this device. Note that the values shown are the recommended and tested operating conditions. Proper device operation outside these conditions is not guaranteed.

Table 2. Recommended Operating Conditions

Characteristic		Symbol	Recommended Value	Unit	Notes
Core supply voltage		V_{DD}	$1.1\text{ V} \pm 55\text{ mV}$	V	—
PLL supply voltage		AV_{DD}	$1.1\text{ V} \pm 55\text{ mV}$	V	1
Core power supply for SerDes transceivers		SV_{DD}	$1.1\text{ V} \pm 55\text{ mV}$	V	—
Pad power supply for SerDes transceivers		XV_{DD}	$1.1\text{ V} \pm 55\text{ mV}$	V	—
DDR SDRAM Controller I/O supply voltage	DDR2 SDRAM Interface	GV_{DD}	$1.8\text{ V} \pm 90\text{ mV}$	V	—
	DDR3 SDRAM Interface		$1.5\text{ V} \pm 75\text{ mV}$		—
Three-speed Ethernet I/O voltage		LV_{DD}	$3.3\text{ V} \pm 165\text{ mV}$ $2.5\text{ V} \pm 125\text{ mV}$	V	4
		TV_{DD}	$3.3\text{ V} \pm 165\text{ mV}$ $2.5\text{ V} \pm 125\text{ mV}$		4
DUART, system control and power management, I ² C, and JTAG I/O voltage		OV_{DD}	$3.3\text{ V} \pm 165\text{ mV}$	V	3
Local bus and GPIO I/O voltage		BV_{DD}	$3.3\text{ V} \pm 165\text{ mV}$ $2.5\text{ V} \pm 125\text{ mV}$ $1.8\text{ V} \pm 90\text{ mV}$	V	—
Input voltage	DDR2 and DDR3 SDRAM Interface signals	MV_{IN}	GND to GV_{DD}	V	2
	DDR2 and DDR3 SDRAM Interface reference	MV_{REF}/n	$GV_{DD}/2 \pm 1\%$	V	—
	Three-speed Ethernet signals	LV_{IN} TV_{IN}	GND to LV_{DD} GND to TV_{DD}	V	4
	Local bus and GPIO signals	BV_{IN}	GND to BV_{DD}	V	—
	Local bus, DUART, SYSCLK, Serial RapidIO, system control and power management, I ² C, and JTAG signals	OV_{IN}	GND to OV_{DD}	V	3
Junction temperature range		T_J	0 to 105	°C	—

Notes:

1. This voltage is the input to the filter discussed in [Section 21.2.1, “PLL Power Supply Filtering,”](#) and not necessarily the voltage at the AV_{DD} pin, that may be reduced from V_{DD} by the filter.
2. **Caution:** MV_{IN} must not exceed GV_{DD} by more than 0.3 V. This limit may be exceeded for a maximum of 20 ms during power-on reset and power-down sequences.
3. **Caution:** OV_{IN} must not exceed OV_{DD} by more than 0.3 V. This limit may be exceeded for a maximum of 20 ms during power-on reset and power-down sequences.
4. **Caution:** L/TV_{IN} must not exceed L/TV_{DD} by more than 0.3 V. This limit may be exceeded for a maximum of 20 ms during power-on reset and power-down sequences.

Table 11. DDR2 SDRAM Interface DC Electrical Characteristics for $GV_{DD}(typ) = 1.8\text{ V}$ (continued)

Parameter/Condition	Symbol	Min	Max	Unit	Notes
Output low current ($V_{OUT} = 0.280\text{ V}$)	I_{OL}	13.4	—	mA	—

Notes:

1. GV_{DD} is expected to be within 50 mV of the DRAM GV_{DD} at all times.
2. MV_{REFn} is expected to be equal to $0.5 \times GV_{DD}$, and to track GV_{DD} DC variations as measured at the receiver.
Peak-to-peak noise on MV_{REFn} may not exceed $\pm 2\%$ of the DC value.
3. V_{TT} is not applied directly to the device. It is the supply to that far end signal termination is made and is expected to be equal to MV_{REFn} . This rail should track variations in the DC level of MV_{REFn} .
4. Output leakage is measured with all outputs disabled, $0\text{ V} \leq V_{OUT} \leq GV_{DD}$.

Table 12 provides the recommended operating conditions for the DDR SDRAM controller of the MPC8572E when interfacing to DDR3 SDRAM.

Table 12. DDR3 SDRAM Interface DC Electrical Characteristics for $GV_{DD}(typ) = 1.5\text{ V}$

Parameter/Condition	Symbol	Min	Typical	Max	Unit
I/O supply voltage	GV_{DD}	1.425	1.575	V	1
I/O reference voltage	MV_{REFn}	$0.49 \times GV_{DD}$	$0.51 \times GV_{DD}$	V	2
Input high voltage	V_{IH}	$MV_{REFn} + 0.100$	GV_{DD}	V	—
Input low voltage	V_{IL}	GND	$MV_{REFn} - 0.100$	V	—
Output leakage current	I_{OZ}	–50	50	μA	3

Notes:

1. GV_{DD} is expected to be within 50 mV of the DRAM GV_{DD} at all times.
2. MV_{REFn} is expected to be equal to $0.5 \times GV_{DD}$, and to track GV_{DD} DC variations as measured at the receiver.
Peak-to-peak noise on MV_{REFn} may not exceed $\pm 1\%$ of the DC value.
3. Output leakage is measured with all outputs disabled, $0\text{ V} \leq V_{OUT} \leq GV_{DD}$.

Table 13 provides the DDR SDRAM controller interface capacitance for DDR2 and DDR3.

Table 13. DDR2 and DDR3 SDRAM Interface Capacitance for $GV_{DD}(typ)=1.8\text{ V}$ and 1.5 V

Parameter/Condition	Symbol	Min	Typical	Max	Unit
Input/output capacitance: DQ, DQS, $\overline{DQS}$	C_{IO}	6	8	pF	1, 2
Delta input/output capacitance: DQ, DQS, $\overline{DQS}$	C_{DIO}	—	0.5	pF	1, 2

Note:

1. This parameter is sampled. $GV_{DD} = 1.8\text{ V} \pm 0.090\text{ V}$ (for DDR2), $f = 1\text{ MHz}$, $T_A = 25^\circ\text{C}$, $V_{OUT} = GV_{DD}/2$, V_{OUT} (peak-to-peak) = 0.2 V.
2. This parameter is sampled. $GV_{DD} = 1.5\text{ V} \pm 0.075\text{ V}$ (for DDR3), $f = 1\text{ MHz}$, $T_A = 25^\circ\text{C}$, $V_{OUT} = GV_{DD}/2$, V_{OUT} (peak-to-peak) = 0.175 V.

Table 17. DDR2 and DDR3 SDRAM Interface Input AC Timing Specifications

At recommended operating conditions with GV_{DD} of 1.8 V $\pm$ 5% for DDR2 or 1.5 V $\pm$ 5% for DDR3.

Parameter	Symbol	Min	Max	Unit	Notes
Controller Skew for MDQS—MDQ/MECC	t_{CISKEW}	—	—	ps	1, 2
800 MHz	—	–200	200	—	—
667 MHz	—	–240	240	—	—
533 MHz	—	–300	300	—	—
400 MHz	—	–365	365	—	—

Note:

1. t_{CISKEW} represents the total amount of skew consumed by the controller between MDQS[n] and any corresponding bit that is captured with MDQS[n]. This should be subtracted from the total timing budget.
2. The amount of skew that can be tolerated from MDQS to a corresponding MDQ signal is called t_{DISKEW} . This can be determined by the following equation: $t_{DISKEW} = \pm(T/4 - \text{abs}(t_{CISKEW}))$ where T is the clock period and $\text{abs}(t_{CISKEW})$ is the absolute value of t_{CISKEW} .

Figure 3 shows the DDR2 and DDR3 SDRAM interface input timing diagram.

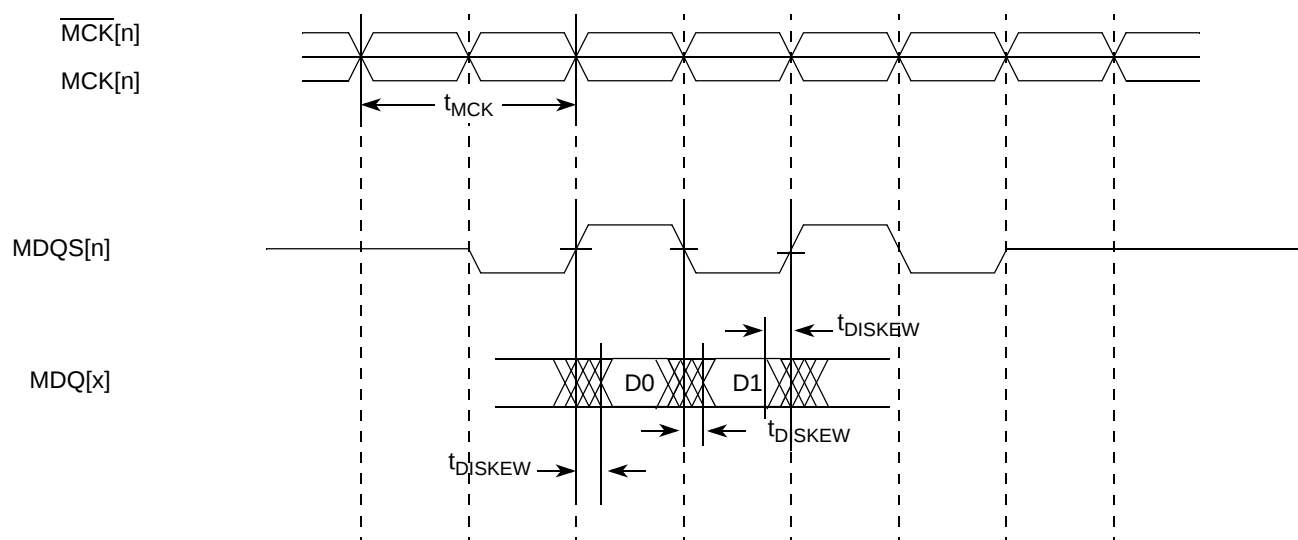


Figure 3. DDR2 and DDR3 SDRAM Interface Input Timing Diagram

6.2.2 DDR2 and DDR3 SDRAM Interface Output AC Timing Specifications

Table 18 contains the output AC timing targets for the DDR2 and DDR3 SDRAM interface.

Table 18. DDR2 and DDR3 SDRAM Interface Output AC Timing Specifications

At recommended operating conditions with GV_{DD} of 1.8 V $\pm$ 5% for DDR2 or 1.5 V $\pm$ 5% for DDR3.

Parameter	Symbol ¹	Min	Max	Unit	Notes
MCK[n] cycle time	t_{MCK}	2.5	5	ns	2
ADDR/CMD output setup with respect to MCK	t_{DDKHAS}			ns	3

Table 24. MII, GMII, RMII, RGMII, TBI, RTBI, and FIFO DC Electrical Characteristics (continued)

Parameters	Symbol	Min	Max	Unit	Notes
Input high current ($V_{IN} = LV_{DD}$, $V_{IN} = TV_{DD}$)	I_{IH}	—	10	μA	1, 2,3
Input low current ($V_{IN} = GND$)	I_{IL}	–15	—	μA	3

Note:

- ¹ LV_{DD} supports eTSECs 1 and 2.
- ² TV_{DD} supports eTSECs 3 and 4 or FEC.
- ³ Note that the symbol V_{IN} , in this case, represents the LV_{IN} and TV_{IN} symbols referenced in [Table 1](#).

8.2 FIFO, GMII, MII, TBI, RGMII, RMII, and RTBI AC Timing Specifications

The AC timing specifications for FIFO, GMII, MII, TBI, RGMII, RMII and RTBI are presented in this section.

8.2.1 FIFO AC Specifications

The basis for the AC specifications for the eTSEC's FIFO modes is the double data rate RGMII and RTBI specifications, because they have similar performance and are described in a source-synchronous fashion like FIFO modes. However, the FIFO interface provides deliberate skew between the transmitted data and source clock in GMII fashion.

When the eTSEC is configured for FIFO modes, all clocks are supplied from external sources to the relevant eTSEC interface. That is, the transmit clock must be applied to the eTSECn's TSECn_TX_CLK, while the receive clock must be applied to pin TSECn_RX_CLK. The eTSEC internally uses the transmit clock to synchronously generate transmit data and outputs an echoed copy of the transmit clock back on the TSECn_GTX_CLK pin (while transmit data appears on TSECn_TXD[7:0], for example). It is intended that external receivers capture eTSEC transmit data using the clock on TSECn_GTX_CLK as a source-synchronous timing reference. Typically, the clock edge that launched the data can be used, because the clock is delayed by the eTSEC to allow acceptable set-up margin at the receiver. Note that there is a relationship between the maximum FIFO speed and the platform (CCB) frequency. For more information see [Section 4.5, "Platform to eTSEC FIFO Restrictions."](#)

[Table 25](#) and [Table 26](#) summarize the FIFO AC specifications.

Table 25. FIFO Mode Transmit AC Timing Specification

At recommended operating conditions with LV_{DD}/TV_{DD} of $2.5V \pm 5\%$

Parameter/Condition	Symbol	Min	Typ	Max	Unit
TX_CLK, GTX_CLK clock period ¹	t_{FIT}	5.3	8.0	100	ns
TX_CLK, GTX_CLK duty cycle	t_{FITH}/t_{FIT}	45	50	55	%

Figure 12 shows the MII transmit AC timing diagram.

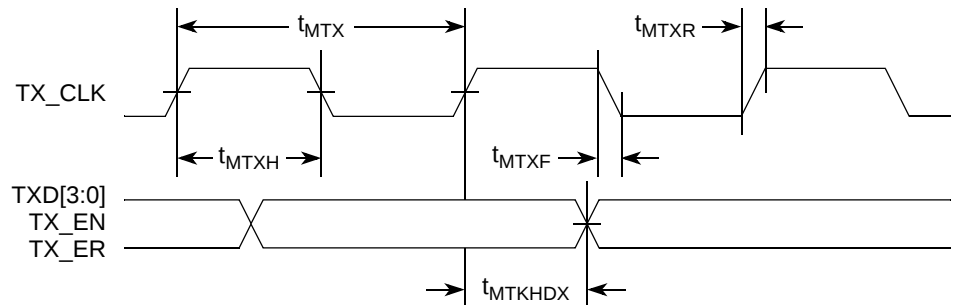


Figure 12. MII Transmit AC Timing Diagram

8.2.3.2 MII Receive AC Timing Specifications

Table 30 provides the MII receive AC timing specifications.

Table 30. MII Receive AC Timing Specifications

At recommended operating conditions with V_{DD}/V_{DD} of 2.5/ 3.3 V $\pm$ 5%.

Parameter/Condition	Symbol ¹	Min	Typ	Max	Unit
RX_CLK clock period 10 Mbps	t_{MRX}^2	—	400	—	ns
RX_CLK clock period 100 Mbps	t_{MRX}	—	40	—	ns
RX_CLK duty cycle	t_{MRXH}/t_{MRX}	35	—	65	%
RXD[3:0], RX_DV, RX_ER setup time to RX_CLK	t_{MRDVKH}	10.0	—	—	ns
RXD[3:0], RX_DV, RX_ER hold time to RX_CLK	t_{MRDXKH}	10.0	—	—	ns
RX_CLK clock rise (20%-80%)	t_{MRXR}^2	1.0	—	4.0	ns
RX_CLK clock fall time (80%-20%)	t_{MRXF}^2	1.0	—	4.0	ns

Notes:

1. The symbols used for timing specifications herein follow the pattern of $t_{(first\ two\ letters\ of\ functional\ block)(signal)(state)\ (reference)(state)}$ for inputs and $t_{(first\ two\ letters\ of\ functional\ block)(reference)(state)(signal)(state)}$ for outputs. For example, t_{MRDVKH} symbolizes MII receive timing (MR) with respect to the time data input signals (D) reach the valid state (V) relative to the t_{MRX} clock reference (K) going to the high (H) state or setup time. Also, t_{MRDXKL} symbolizes MII receive timing (GR) with respect to the time data input signals (D) went invalid (X) relative to the t_{MRX} clock reference (K) going to the low (L) state or hold time. Note that, in general, the clock reference symbol representation is based on three letters representing the clock of a particular functional. For example, the subscript of t_{MRX} represents the MII (M) receive (RX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
2. Guaranteed by design.

Figure 13 provides the AC test load for eTSEC.

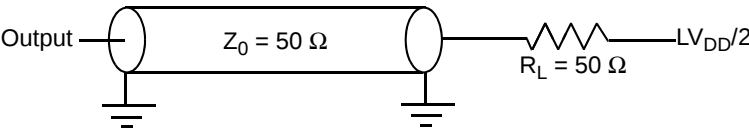


Figure 13. eTSEC AC Test Load

Figure 18 shows the RGMII and RTBI AC timing and multiplexing diagrams.

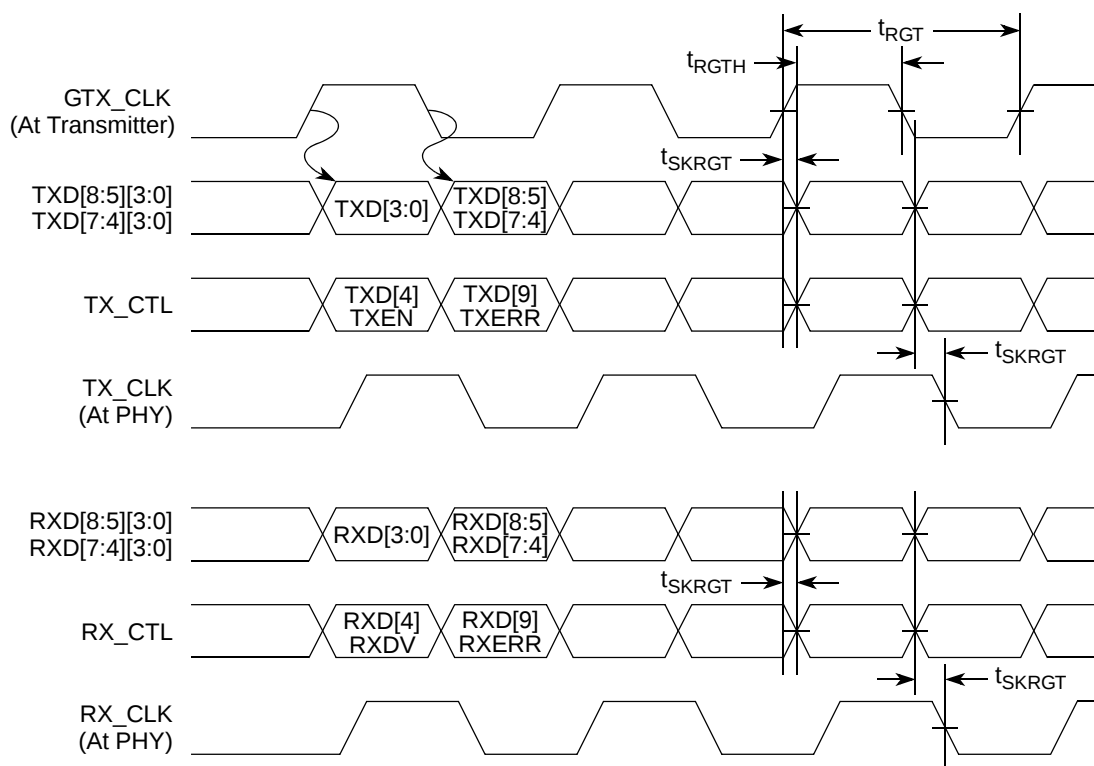


Figure 18. RGMII and RTBI AC Timing and Multiplexing Diagrams

8.2.7 RMII AC Timing Specifications

This section describes the RMII transmit and receive AC timing specifications.

8.2.7.1 RMII Transmit AC Timing Specifications

Table 35 shows the RMII transmit AC timing specifications.

Table 35. RMII Transmit AC Timing Specifications

At recommended operating conditions with LV_{DD}/TV_{DD} of 2.5/ 3.3 V $\pm$ 5%.

Parameter/Condition	Symbol ¹	Min	Typ	Max	Unit
TSECn_TX_CLK clock period	t_{RMT}	15.0	20.0	25.0	ns
TSECn_TX_CLK duty cycle	t_{RMTH}	35	50	65	%
TSECn_TX_CLK peak-to-peak jitter	t_{RMTJ}	—	—	250	ps
Rise time TSECn_TX_CLK (20%–80%)	t_{RMTR}	1.0	—	2.0	ns
Fall time TSECn_TX_CLK (80%–20%)	t_{RMTE}	1.0	—	2.0	ns

Table 43. MII Management DC Electrical Characteristics (LV_{DD}/TV_{DD}=3.3 V) (continued)

Parameter	Symbol	Min	Max	Unit	Notes
Input low current (LV _{DD} /TV _{DD} = Max, V _{IN} = 0.5 V)	I _{IL}	−600	—	μA	—

Note:

1. EC1_MDC and EC1_MDIO operate on LV_{DD}.
2. EC3_MDC & EC3_MDIO and EC5_MDC & EC5_MDIO operate on TV_{DD}.
3. Note that the symbol V_{IN}, in this case, represents the LV_{IN} and TV_{IN} symbol referenced in [Table 1](#).

Table 44. MII Management DC Electrical Characteristics (LV_{DD}/TV_{DD}=2.5 V)

Parameters	Symbol	Min	Max	Unit	Notes
Supply voltage 2.5 V	LV _{DD} /TV _{DD}	2.37	2.63	V	1,2
Output high voltage (LV _{DD} /TV _{DD} = Min, I _{OH} = −1.0 mA)	V _{OH}	2.00	LV _{DD} /TV _{DD} + 0.3	V	—
Output low voltage (LV _{DD} /TV _{DD} = Min, I _{OL} = 1.0 mA)	V _{OL}	GND − 0.3	0.40	V	—
Input high voltage	V _{IH}	1.70	LV _{DD} /TV _{DD} + 0.3	V	—
Input low voltage	V _{IL}	−0.3	0.70	V	—
Input high current (V _{IN} = LV _{DD} , V _{IN} = TV _{DD})	I _{IH}	—	10	μA	1, 2,3
Input low current (V _{IN} = GND)	I _{IL}	−15	—	μA	3

Note:

1. EC1_MDC and EC1_MDIO operate on LV_{DD}.
2. EC3_MDC & EC3_MDIO and EC5_MDC & EC5_MDIO operate on TV_{DD}.
3. Note that the symbol V_{IN}, in this case, represents the LV_{IN} and TV_{IN} symbols referenced in [Table 1](#).

9.2 MII Management AC Electrical Specifications

[Table 45](#) provides the MII management AC timing specifications. There are three sets of Ethernet management signals (EC1_MDC and EC1_MDIO, EC3_MDC and EC3_MDIO, EC5_MDC and EC5_MDIO). These are not explicitly shown in the table or in the figure following.

Table 45. MII Management AC Timing Specifications

At recommended operating conditions with LV_{DD}/TV_{DD} of 3.3 V ± 5% or 2.5 V ± 5%.

Parameter/Condition	Symbol ¹	Min	Typ	Max	Unit	Notes
ECn_MDC frequency	f _{MDC}	0.9	2.5	9.3	MHz	2, 3
ECn_MDC period	t _{MDC}	107.5	—	1120	ns	—
ECn_MDC clock pulse width high	t _{MDCH}	32	—	—	ns	—
ECn_MDC to ECn_MDIO delay	t _{MDKHDX}	10	—	16*t _{plb_clk}	ns	5

Table 53. JTAG AC Timing Specifications (Independent of SYSCLK) ¹ (continued)

At recommended operating conditions with OV_{DD} of 3.3 V $\pm$ 5%.

Parameter	Symbol ²	Min	Max	Unit	Notes
JTAG external clock to output high impedance:				ns	
Boundary-scan data	t_{JTKLDZ}	3	19		5, 6
TDO	t_{JTKLOZ}	3	9		

Notes:

1. All outputs are measured from the midpoint voltage of the falling/rising edge of t_{TCLK} to the midpoint of the signal in question. The output timings are measured at the pins. All output timings assume a purely resistive 50- Ω load (see Figure 36). Time-of-flight delays must be added for trace lengths, vias, and connectors in the system.
2. The symbols used for timing specifications herein follow the pattern of $t_{(first\ two\ letters\ of\ functional\ block)(signal)(state)\ (reference)(state)}$ for inputs and $t_{(first\ two\ letters\ of\ functional\ block)(reference)(state)(signal)(state)}$ for outputs. For example, $t_{JTDV KH}$ symbolizes JTAG device timing (JT) with respect to the time data input signals (D) reaching the valid state (V) relative to the t_{JTG} clock reference (K) going to the high (H) state or setup time. Also, $t_{JTDX KH}$ symbolizes JTAG timing (JT) with respect to the time data input signals (D) went invalid (X) relative to the t_{JTG} clock reference (K) going to the high (H) state. Note that, in general, the clock reference symbol representation is based on three letters representing the clock of a particular functional. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
3. TRST is an asynchronous level sensitive signal. The setup time is for test purposes only.
4. Non-JTAG signal input timing with respect to t_{TCLK} .
5. Non-JTAG signal output timing with respect to t_{TCLK} .
6. Guaranteed by design.

Figure 36 provides the AC test load for TDO and the boundary-scan outputs.

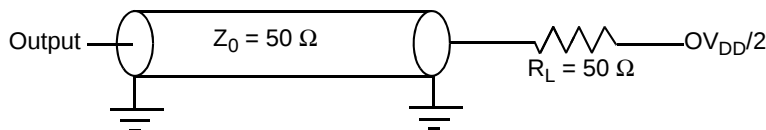

Figure 36. AC Test Load for the JTAG Interface

Figure 37 provides the JTAG clock input timing diagram.

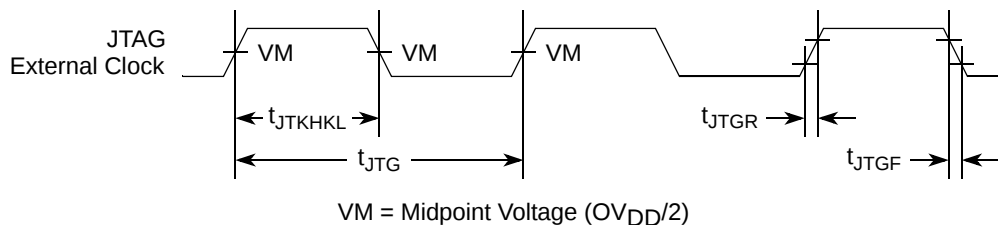

Figure 37. JTAG Clock Input Timing Diagram

Figure 38 provides the $\overline{TRST}$ timing diagram.

- To meet the input amplitude requirement, the reference clock inputs might need to be DC or AC-coupled externally. For the best noise performance, the reference of the clock could be DC or AC-coupled into the unused phase ($\overline{\text{SDn_REF_CLK}}$) through the same source impedance as the clock input (SDn_REF_CLK) in use.

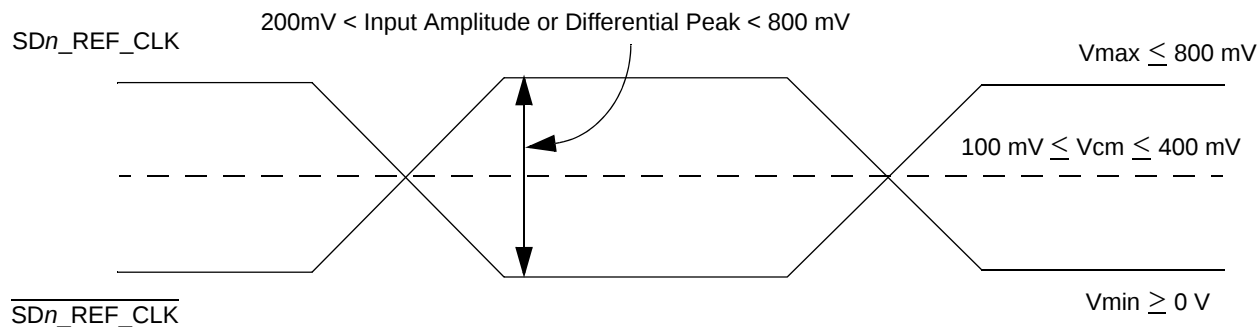


Figure 45. Differential Reference Clock Input DC Requirements (External DC-Coupled)

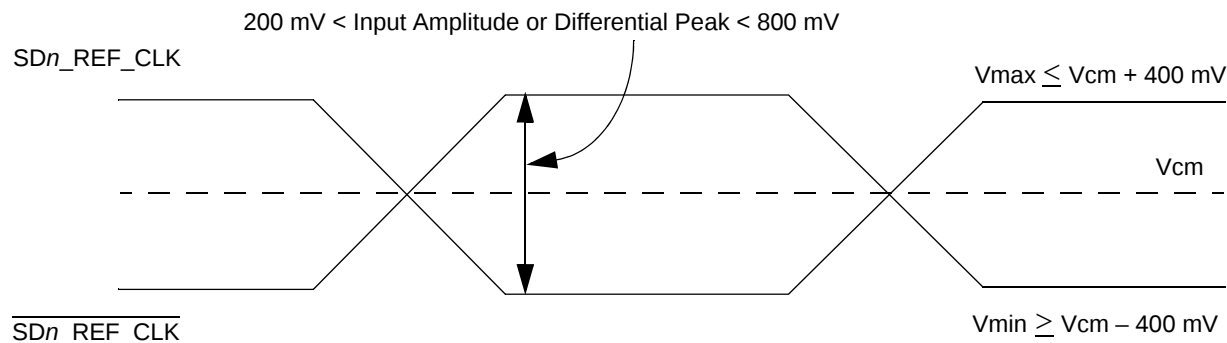


Figure 46. Differential Reference Clock Input DC Requirements (External AC-Coupled)

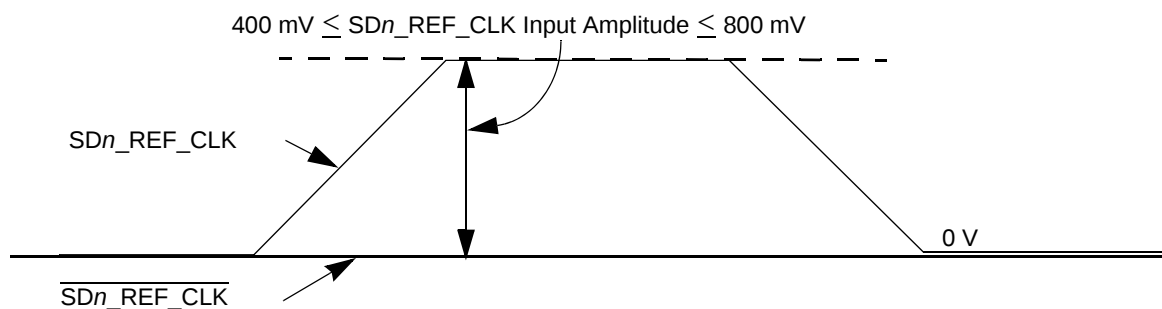


Figure 47. Single-Ended Reference Clock Input DC Requirements

Table 63. Differential Receiver (RX) Input Specifications (continued)

Symbol	Parameter	Min	Nominal	Max	Units	Comments
$T_{RX-EYE-MEDIAN-to-MAX-JITTER}$	Maximum time between the jitter median and maximum deviation from the median.	—	—	0.3	UI	Jitter is defined as the measurement variation of the crossing points ($V_{RX-DIFFp-p} = 0$ V) in relation to a recovered TX UI. A recovered TX UI is calculated over 3500 consecutive unit intervals of sample data. Jitter is measured using all edges of the 250 consecutive UI in the center of the 3500 UI used for calculating the TX UI. See Notes 2, 3 and 7.
$V_{RX-CM-ACp}$	AC Peak Common Mode Input Voltage	—	—	150	mV	$V_{RX-CM-ACp} = V_{RXD+} + V_{RXD-} /2 - V_{RX-CM-DC}$ $V_{RX-CM-DC} = DC_{(avg)}$ of $ V_{RX-D+} + V_{RX-D-} /2$ See Note 2
$RL_{RX-DIFF}$	Differential Return Loss	15	—	—	dB	Measured over 50 MHz to 1.25 GHz with the D+ and D- lines biased at +300 mV and -300 mV, respectively. See Note 4
RL_{RX-CM}	Common Mode Return Loss	6	—	—	dB	Measured over 50 MHz to 1.25 GHz with the D+ and D- lines biased at 0 V. See Note 4
$Z_{RX-DIFF-DC}$	DC Differential Input Impedance	80	100	120	Ω	RX DC Differential mode impedance. See Note 5
Z_{RX-DC}	DC Input Impedance	40	50	60	Ω	Required RX D+ as well as D- DC Impedance ($50 \pm 20\%$ tolerance). See Notes 2 and 5.
$Z_{RX-HIGH-IMP-DC}$	Powered Down DC Input Impedance	200 k	—	—	Ω	Required RX D+ as well as D- DC Impedance when the Receiver terminations do not have power. See Note 6.
$V_{RX-IDLE-DET-DIFFp-p}$	Electrical Idle Detect Threshold	65	—	175	mV	$V_{RX-IDLE-DET-DIFFp-p} = 2 * V_{RX-D+} - V_{RX-D-} $ Measured at the package pins of the Receiver
$T_{RX-IDLE-DET-DIFF-ENTERTIME}$	Unexpected Electrical Idle Enter Detect Threshold Integration Time	—	—	10	ms	An unexpected Electrical Idle ($V_{RX-DIFFp-p} < V_{RX-IDLE-DET-DIFFp-p}$) must be recognized no longer than $T_{RX-IDLE-DET-DIFF-ENTERING}$ to signal an unexpected idle condition.

Table 66. Short Run Transmitter AC Timing Specifications—2.5 Gbaud (continued)

Characteristic	Symbol	Range		Unit	Notes
		Min	Max		
Multiple Output skew	S_{MO}	—	1000	ps	Skew at the transmitter output between lanes of a multilane link
Unit Interval	UI	400	400	ps	+/- 100 ppm

Table 67. Short Run Transmitter AC Timing Specifications—3.125 Gbaud

Characteristic	Symbol	Range		Unit	Notes
		Min	Max		
Output Voltage,	V_O	−0.40	2.30	Volts	Voltage relative to COMMON of either signal comprising a differential pair
Differential Output Voltage	V_{DIFFPP}	500	1000	mV p-p	—
Deterministic Jitter	J_D	—	0.17	UI p-p	—
Total Jitter	J_T	—	0.35	UI p-p	—
Multiple output skew	S_{MO}	—	1000	ps	Skew at the transmitter output between lanes of a multilane link
Unit Interval	UI	320	320	ps	+/- 100 ppm

Table 68. Long Run Transmitter AC Timing Specifications—1.25 Gbaud

Characteristic	Symbol	Range		Unit	Notes
		Min	Max		
Output Voltage,	V_O	−0.40	2.30	Volts	Voltage relative to COMMON of either signal comprising a differential pair
Differential Output Voltage	V_{DIFFPP}	800	1600	mV p-p	—
Deterministic Jitter	J_D	—	0.17	UI p-p	—
Total Jitter	J_T	—	0.35	UI p-p	—
Multiple output skew	S_{MO}	—	1000	ps	Skew at the transmitter output between lanes of a multilane link
Unit Interval	UI	800	800	ps	+/- 100 ppm

Table 74. Receiver AC Timing Specifications—3.125 GBaud

Characteristic	Symbol	Range		Unit	Notes
		Min	Max		
Differential Input Voltage	V_{IN}	200	1600	mV p-p	Measured at receiver
Deterministic Jitter Tolerance	J_D	0.37	—	UI p-p	Measured at receiver
Combined Deterministic and Random Jitter Tolerance	J_{DR}	0.55	—	UI p-p	Measured at receiver
Total Jitter Tolerance ¹	J_T	0.65	—	UI p-p	Measured at receiver
Multiple Input Skew	S_{MI}	—	22	ns	Skew at the receiver input between lanes of a multilane link
Bit Error Rate	BER	—	10^{-12}	—	—
Unit Interval	UI	320	320	ps	+/- 100 ppm

Note:

1. Total jitter is composed of three components, deterministic jitter, random jitter and single frequency sinusoidal jitter. The sinusoidal jitter may have any amplitude and frequency in the unshaded region of [Figure 59](#). The sinusoidal jitter component is included to ensure margin for low frequency jitter, wander, noise, crosstalk and other variable system effects.

link shall be active in both the transmit and receive directions, and opposite ends of the links shall use asynchronous clocks. Four lane implementations shall use CJPAT as defined in Annex 48A. Single lane implementations shall use the CJPAT sequence specified in Annex 48A for transmission on lane 0. The amount of data represented in the eye shall be adequate to ensure that the bit error ratio is less than 10^{-12} . The eye pattern shall be measured with AC coupling and the compliance template centered at 0 Volts differential. The left and right edges of the template shall be aligned with the mean zero crossing points of the measured data eye. The load for this test shall be $100\ \Omega$ resistive $\pm 5\%$ differential to 2.5 GHz.

17.8.2 Jitter Test Measurements

For the purpose of jitter measurement, the effects of a single-pole high pass filter with a 3 dB point at (Baud Frequency)/1667 is applied to the jitter. The data pattern for jitter measurements is the Continuous Jitter Test Pattern (CJPAT) pattern defined in Annex 48A of IEEE 802.3ae. All lanes of the LP-Serial link shall be active in both the transmit and receive directions, and opposite ends of the links shall use asynchronous clocks. Four lane implementations shall use CJPAT as defined in Annex 48A. Single lane implementations shall use the CJPAT sequence specified in Annex 48A for transmission on lane 0. Jitter shall be measured with AC coupling and at 0 Volts differential. Jitter measurement for the transmitter (or for calibration of a jitter tolerance setup) shall be performed with a test procedure resulting in a BER curve such as that described in Annex 48B of IEEE 802.3ae.

17.8.3 Transmit Jitter

Transmit jitter is measured at the driver output when terminated into a load of $100\ \Omega$ resistive $\pm 5\%$ differential to 2.5 GHz.

17.8.4 Jitter Tolerance

Jitter tolerance is measured at the receiver using a jitter tolerance test signal. This signal is obtained by first producing the sum of deterministic and random jitter defined in [Section 17.6, “Receiver Specifications,”](#) and then adjusting the signal amplitude until the data eye contacts the 6 points of the minimum eye opening of the receive template shown in [Figure 60](#) and [Table 75](#). Note that for this to occur, the test signal must have vertical waveform symmetry about the average value and have horizontal symmetry (including jitter) about the mean zero crossing. Eye template measurement requirements are as defined above. Random jitter is calibrated using a high pass filter with a low frequency corner at 20 MHz and a 20 dB/decade roll-off below this. The required sinusoidal jitter specified in [Section 17.6, “Receiver Specifications,”](#) is then added to the signal and the test load is replaced by the receiver being tested.

18 Package Description

This section describes package parameters, pin assignments, and dimensions.

5. Datum A, the seating plane, is determined by the spherical crowns of the solder balls.
6. Parallelism measurement shall exclude any effect of mark on top surface of package.

18.3 Pinout Listings

Table 76 provides the pin-out listing for the MPC8572E 1023 FC-PBGA package.

Table 76. MPC8572E Pinout Listing

Signal	Signal Name	Package Pin Number	Pin Type	Power Supply	Notes
DDR SDRAM Memory Interface 1					
D1_MDQ[0:63]	Data	D15, A14, B12, D12, A15, B15, B13, C13, C11, D11, D9, A8, A12, A11, A9, B9, F11, G12, K11, K12, E10, E9, J11, J10, G8, H10, L10, M11, F10, G9, K9, K8, AC6, AC7, AG8, AH9, AB6, AB8, AE9, AF9, AL8, AM8, AM10, AK11, AH8, AK8, AJ10, AK10, AL12, AJ12, AL14, AK14, AL11, AM11, AK13, AM14, AM15, AJ16, AL18, AM18, AJ15, AL15, AK17, AM17	I/O	GV _{DD}	—
D1_MECC[0:7]	Error Correcting Code	M10, M7, R8, T11, L12, L11, P9, R10	I/O	GV _{DD}	—
D1_MAPAR_ERR	Address Parity Error	P6	I	GV _{DD}	—
D1_MAPAR_OUT	Address Parity Out	W6	O	GV _{DD}	—
D1_MDM[0:8]	Data Mask	C14, A10, G11, H9, AD7, AJ9, AM12, AK16, N11	O	GV _{DD}	—
D1_MDQS[0:8]	Data Strobe	A13, C10, H12, J7, AE8, AM9, AM13, AL17, N9	I/O	GV _{DD}	—
D1_MDQS[0:8]	Data Strobe	D14, B10, H13, J8, AD8, AL9, AJ13, AM16, P10	I/O	GV _{DD}	—
D1_MA[0:15]	Address	Y7, W8, U6, W9, U7, V8, Y11, V10, T6, V11, AA10, U9, U10, AD11, T8, P7	O	GV _{DD}	—
D1_MBA[0:2]	Bank Select	AA7, AA8, R7	O	GV _{DD}	—
D1_MWE	Write Enable	AC12	O	GV _{DD}	—

Table 76. MPC8572E Pinout Listing (continued)

Signal	Signal Name	Package Pin Number	Pin Type	Power Supply	Notes
N/C	No Connection	A16, A20, B16, B17, B19, B20, C17, C18, C19, D28, R31, T17, V23, W23, Y22, Y23, Y24, AA24, AB24, AC24, AC26, AC27, AC29, AD31, AE29, AJ25, AK28, AL31, AM21	—	—	17

Note:

1. All multiplexed signals are listed only once and do not re-occur. For example, LCS5/DMA_REQ2 is listed only once in the local bus controller section, and is not mentioned in the DMA section even though the pin also functions as DMA_REQ2.
2. Recommend a weak pull-up resistor (2–10 K Ω) be placed on this pin to OVDD.
4. This pin is an open drain signal.
5. This pin is a reset configuration pin. It has a weak internal pull-up P-FET which is enabled only when the processor is in the reset state. This pull-up is designed such that it can be overpowered by an external 4.7-k Ω pull-down resistor. However, if the signal is intended to be high after reset, and if there is any device on the net which might pull down the value of the net at reset, then a pullup or active driver is needed.
6. Treat these pins as no connects (NC) unless using debug address functionality.
7. The value of LA[29:31] during reset sets the CCB clock to SYSCLK PLL ratio. These pins require 4.7-k Ω pull-up or pull-down resistors. See Section 19.2, “CCB/SYSCLK PLL Ratio.”
8. The value of LALE, LGPL2 and LBCTL at reset set the e500 core clock to CCB Clock PLL ratio. These pins require 4.7-k Ω pull-up or pull-down resistors. See the Section 19.3, “e500 Core PLL Ratio.”
9. Functionally, this pin is an output, but structurally it is an I/O because it either samples configuration input during reset or because it has other manufacturing test functions. This pin therefore be described as an I/O for boundary scan.
10. If this pin is configured for local bus controller usage, recommend a weak pull-up resistor (2-10 K Ω) be placed on this pin to BVDD, to ensure no random chip select assertion due to possible noise and so on.
11. This output is actively driven during reset rather than being three-stated during reset.
12. These JTAG pins have weak internal pull-up P-FETs that are always enabled.
13. These pins are connected to the VDD/GND planes internally and may be used by the core power supply to improve tracking and regulation.
14. Internal thermally sensitive diode.
15. If this pin is connected to a device that pulls down during reset, an external pull-up is required to drive this pin to a safe state during reset.
16. This pin is only an output in FIFO mode when used as Rx Flow Control.
17. Do not connect.
18. These are test signals for factory use only and must be pulled up (100 Ω - 1 K Ω) to OVDD for normal machine operation.
19. Independent supplies derived from board VDD.
20. Recommend a pull-up resistor (~1 K Ω) be placed on this pin to OVDD.
21. The following pins must NOT be pulled down during power-on reset: DMA1_DACK[0:1], EC5_MDC, HRESET_REQ, TRIG_OUT/READY_P0/QUIESCE, MSRCID[2:4], MDVAL, ASLEEP.
22. This pin requires an external 4.7-k Ω pull-down resistor to prevent PHY from seeing a valid Transmit Enable before it is actively driven.
23. This pin is only an output in eTSEC3 FIFO mode when used as Rx flow control.
24. TSEC2_TXD[1] is used as cfg_dram_type. IT MUST BE VALID AT POWER-UP, EVEN BEFORE HRESET ASSERTION.

Table 81 describes the clock ratio between e500 Core1 and the e500 core complex bus (CCB). This ratio is determined by the binary value of $\overline{\text{LWE}}[0]/\text{LBS}[0]/\text{LFWE}$, $\text{UART_SOUT}[1]$, and READY_P1 signals at power up, as shown in Table 81.

Table 81. e500 Core1 to CCB Clock Ratio

Binary Value of $\overline{\text{LWE}}[0]/\text{LBS}[0]/$ LFWE , $\text{UART_SOUT}[1]$, READY_P1 Signals	e500 Core1:CCB Clock Ratio	Binary Value of $\overline{\text{LWE}}[0]/\text{LBS}[0]/$ LFWE , $\text{UART_SOUT}[1]$, READY_P1 Signals	e500 Core1:CCB Clock Ratio
000	Reserved	100	2:1
001	Reserved	101	5:2 (2.5:1)
010	Reserved	110	3:1
011	3:2 (1.5:1)	111	7:2 (3.5:1)

19.4 DDR/DDRCLK PLL Ratio

The dual DDR memory controller complexes can be synchronous with, or asynchronous to, the CCB, depending on configuration.

Table 82 describes the clock ratio between the DDR memory controller complexes and the DDR PLL reference clock, DDRCLK , which is not the memory bus clock. The DDR memory controller complexes clock frequency is equal to the DDR data rate.

When synchronous mode is selected, the memory buses are clocked at half the CCB clock rate. The default mode of operation is for the DDR data rate for both DDR controllers to be equal to the CCB clock rate in synchronous mode, or the resulting DDR PLL rate in asynchronous mode.

In asynchronous mode, the DDR PLL rate to DDRCLK ratios listed in Table 82 reflects the DDR data rate to DDRCLK ratio, because the DDR PLL rate in asynchronous mode means the DDR data rate resulting from DDR PLL output.

Note that the DDR PLL reference clock input, DDRCLK , is only required in asynchronous mode. MPC8572E does not support running one DDR controller in synchronous mode and the other in asynchronous mode.

Table 82. DDR Clock Ratio

Binary Value of TSEC_1588_CLK_OUT , $\text{TSEC_1588_PULSE_OUT1}$, $\text{TSEC_1588_PULSE_OUT2}$ Signals	DDR:DDRCLK Ratio
000	3:1
001	4:1
010	6:1
011	8:1
100	10:1

Table 85 summarizes the signal impedance targets. The driver impedances are targeted at minimum V_{DD} , nominal OV_{DD} , 105°C.

Table 85. Impedance Characteristics

Impedance	Local Bus, Ethernet, DUART, Control, Configuration, Power Management	DDR DRAM	Symbol	Unit
R_N	45 Target	18 Target (full strength mode) 36 Target (half strength mode)	Z_0	Ω
R_P	45 Target	18 Target (full strength mode) 36 Target (half strength mode)	Z_0	Ω

Note: Nominal supply voltages. See Table 1, $T_j = 105^\circ\text{C}$.

21.8 Configuration Pin Muxing

The MPC8572E provides the user with power-on configuration options which can be set through the use of external pull-up or pull-down resistors of 4.7 k Ω on certain output pins (see customer visible configuration pins). These pins are generally used as output only pins in normal operation.

While $\overline{\text{HRESET}}$ is asserted however, these pins are treated as inputs. The value presented on these pins while $\overline{\text{HRESET}}$ is asserted, is latched when $\overline{\text{HRESET}}$ deasserts, at which time the input receiver is disabled and the I/O circuit takes on its normal function. Most of these sampled configuration pins are equipped with an on-chip gated resistor of approximately 20 k Ω . This value should permit the 4.7-k Ω resistor to pull the configuration pin to a valid logic low level. The pull-up resistor is enabled only during $\overline{\text{HRESET}}$ (and for platform /system clocks after $\overline{\text{HRESET}}$ deassertion to ensure capture of the reset value). When the input receiver is disabled the pull-up is also, thus allowing functional operation of the pin as an output with minimal signal quality or delay disruption. The default value for all configuration bits treated this way has been encoded such that a high voltage level puts the device into the default state and external resistors are needed only when non-default settings are required by the user.

Careful board layout with stubless connections to these pull-down resistors coupled with the large value of the pull-down resistor should minimize the disruption of signal quality or speed for output pins thus configured.

The platform PLL ratio, DDR complex PLL and e500 PLL ratio configuration pins are not equipped with these default pull-up devices.

21.9 JTAG Configuration Signals

Correct operation of the JTAG interface requires configuration of a group of system control pins as demonstrated in Figure 66. Care must be taken to ensure that these pins are maintained at a valid deasserted state under normal operating conditions as most have asynchronous behavior and spurious assertion gives unpredictable results.

Boundary-scan testing is enabled through the JTAG interface signals. The $\overline{\text{TRST}}$ signal is optional in the IEEE Std 1149.1 specification, but it is provided on all processors built on Power Architecture technology. The device requires $\overline{\text{TRST}}$ to be asserted during power-on reset flow to ensure that the JTAG boundary

Table 87. Part Numbering Nomenclature—Rev 2.1

MPC	nnnn	e	t	l	pp	ffm	r
Product Code ¹	Part Identifier	Security Engine	Temperature	Power	Package Sphere Type ²	Processor Frequency/DDR Data Rate ³	Silicon Revision
MPC PPC	8572	E = Included	Blank = 0 to 105°C C = –40 to 105°C	Blank = Standard L = Low	PX = Leaded, FC-PBGA VT = Pb-free, FC-PBGA	AVN = 150-MHz processor; 800 MT/s DDR data rate	D= Ver. 2.1 (SVR = 0x80E8_0021) SEC included
		Blank = Not included				AUL = 1333-MHz processor; 667 MT/s DDR data rate ATL = 1200-MHz processor; 667 MT/s DDR data rate ARL = 1067-MHz processor; 667 MT/s DDR data rate	D= Ver. 2.1 (SVR = 0x80E0_0021) SEC not included

Notes:

- ¹ MPC stands for “Qualified.”
PPC stands for “Prototype”
- ² See [Section 18, “Package Description,”](#) for more information on the available package types.
- ³ Processor core frequencies supported by parts addressed by this specification only. Not all parts described in this specification support all core frequencies. Additionally, parts addressed by part number specifications may support other maximum core frequencies.

Table 88. Part Numbering Nomenclature—Rev 1.1.1

MPC	nnnn	e	t	pp	ffm	r
Product Code ¹	Part Identifier	Security Engine	Temperature	Package Sphere Type ²	Processor Frequency/DDR Data Rate ³	Silicon Revision
MPC PPC	8572	E = Included	Blank=0 to 105°C C= –40 to 105°C	PX = Leaded, FC-PBGA VT = Pb-free, FC-PBGA	AVN = 1500-MHz processor; 800 MT/s DDR data rate AUL = 1333-MHz process or; 667 MT/s DDR datarate ATL = 1200-MHz processor; 667 MT/s DDR data rate ARL = 1067-MHz processor; 667 MT/s DDR data rate	B = Ver. 1.1.1 (SVR = 0x80E8_0011) SEC included
		Blank = Not included				B = Ver. 1.1.1 (SVR = 0x80E0_0011) SEC not included

Notes:

- ¹ MPC stands for “Qualified.”
PPC stands for “Prototype”
- ² See [Section 18, “Package Description,”](#) for more information on the available package types.